# MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED

M28S

# **Product specification**





## FEATURES

- Excellent h<sub>FE</sub> Linearity
- High DC Current Gain

### **Reference News**

PACKAGE OUTLINE	Foot position analysis	Marking
	<ol> <li>BASE</li> <li>EMITTER</li> <li>COLLECTOR</li> </ol>	28S
SOT-23		

### CLASSIFICATION OF hFE(2)

RANK B		С	D
RANGE	300 –550	500 –700	650 – 1000

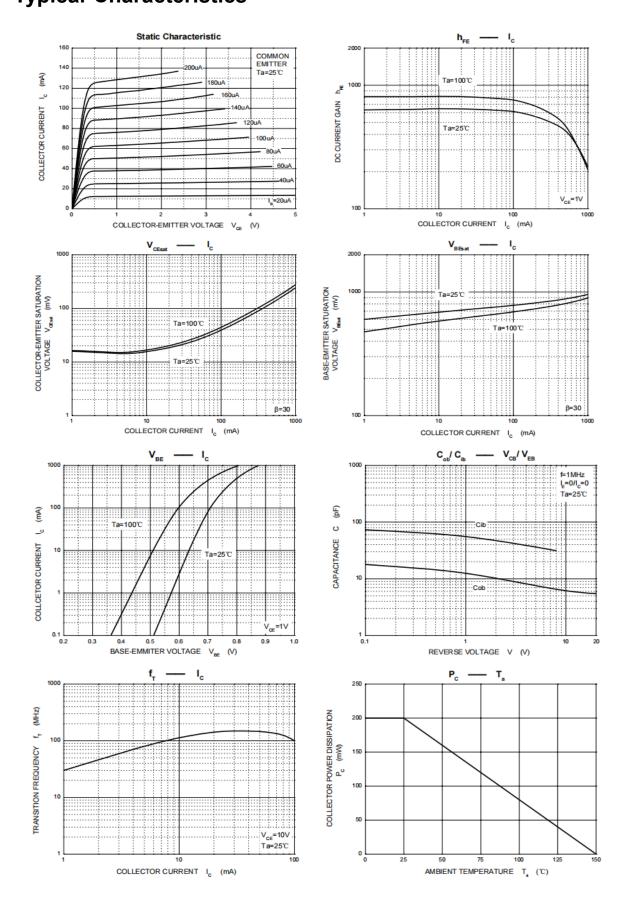
### MAXIMUM RATINGS (Ta=25 $^\circ\!\mathrm{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
Vсво	Collector-Base Voltage	40	V
VCEO	VCEO     Collector-Emitter Voltage       VEBO     Emitter-Base Voltage       Ic     Collector Current       Pc     Collector Power Dissipation		V
VEBO			V
lc			А
Pc			W
R <sub>0JA</sub>	Thermal Resistance From Junction To Ambient	625	°C/W
Tj	T <sub>j</sub> Junction Temperature		ĉ
T <sub>stg</sub> Storage Temperature		-55~+150	ĉ

### ELECTRICAL CHARACTERISTICS (Ta=25 °C unless otherwise specified)

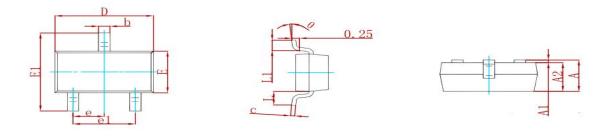
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	Ic=0.1mA, I <sub>E</sub> =0	40			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	20			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =0. 1mA, I <sub>C</sub> =0	6			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =35V, I <sub>E</sub> =0			0.1	А
Collector cut-off current	ICEO	V <sub>CE</sub> =20V, I <sub>B</sub> =0			5	А
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0			0.1	А
	FE(1)	V <sub>CE</sub> =1V, I <sub>C</sub> =1mA	290			
DC current gain	FE(2)	V <sub>CE</sub> =1V, I <sub>C</sub> =100mA	300		1000	
	FE(3)	V <sub>CE</sub> =1V, I <sub>C</sub> =300mA	300			
	FE(4)	V <sub>CE</sub> =1V, I <sub>C</sub> =500mA	300			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	Ic=600mA, I <sub>B</sub> =20mA			0.55	V
Transition frequency	т	V <sub>CE</sub> =10V,I <sub>E</sub> =50mA, f=1MHz	100			MHz
Collector output capacitance	Cob	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		9		pF

# Typical Characteristics



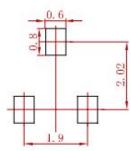


### PACKAGE MECHANICAL DATA



O much al	Dimensions In Millimeters		Dimensior	ns In Inches
Symbol	Min	Max	Min	Max
А	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
С	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.950 TYP		0.03	7 TYP
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022	2 REF
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

# Suggested Pad Layout



#### Note:

1.Controlling dimension:in millimeters.

- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

### **REEL SPECIFICATION**

P/N	PKG	QTY
M28S	SOT-23	3000

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